



Attorney Docket #12/C
1/30/03
SEL 203

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Application of)
NAKAJIMA et al.)
Serial No.: 09/635,945)
Filed: August 10, 2000)
For: Semiconductor Device And Method)
Of Manufacturing The)
Semiconductor Device)
Art Unit: 2811)
Examiner: S. Hu)

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AMENDMENT C

In response to the Final Rejection of November 20, 2002, a RCE being separately requested, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend the claims as follows:

3. (Third Amendment) A semiconductor device comprising:
- a substrate having an insulating surface;
 - a thin film transistor formed over the substrate, the thin-film transistor comprising a gate electrode formed over the substrate; a first insulating layer, wherein a portion of said first insulating layer is formed on said gate electrode; a channel formation region formed in a semiconductor layer